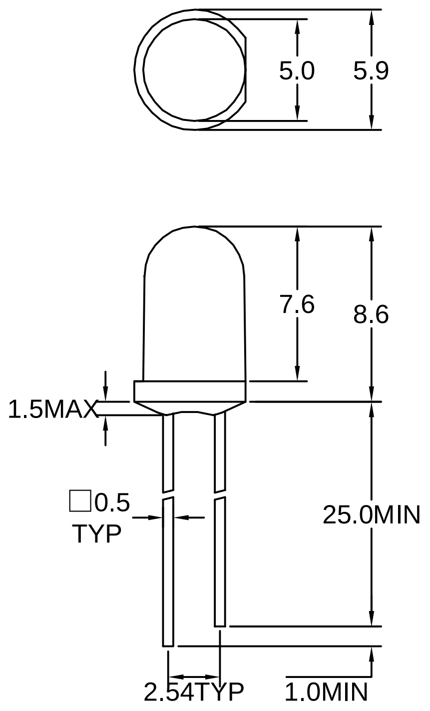
LIGITEK

PHOTO DIODE SILICON PIN LED LAMPS LPD3330 SERIES

Package Dimension



NOTE:1.All dimension are In millimeters tolerance Is ±0.25 unless otherwise noted
2.Specifications are subject to change without notice

Description

The LPD3330 series are silicon planar P/N photodiodes incorporated in plastic package that simultaneously serve as filter and are also Transparent for infrared emission their terminals are soldering tabs arranged in 2.54mm center to center spacing due to their design the diodes can vertically be assembled on pc boards arrays can be realized by multiple arrangement versatile photodetectors are suitable for diodes as well as voltaic cell operation the signal noise ratio is particularly favorable even at low illuminance the P/N photodiode are outstanding for low junction capacitance high cut-off frequency and fast switching times.

They are particularly suitable for IR sound transmission and remote control the cathode of LPD3330 photodiode is marked by a stamping on the package edge

· MAXIMUM RATINGS (TA=25℃)

Characteristic	Symbol	Rating	Unit
Reverse Break Down Voltage	V_{BR}	30	V
Power Dissipation	PD	150	mW
Operating Temperature	Topr	-30 ~ +60	℃
Storage Temperature	Tstg	-40 ~ +60	℃

· ELECTRICAL CHARACTERISTICS AT (TA=℃)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Dark Current	I_D	V_R=10V Ee=0mW/c㎡	—	1.0	30	nA
Short Circuit Current	Isc	V_R=5V λ_P=940nm Ee=0.5mW/c㎡	1.5	2.0	—	uA
Open Circuit Voltage	Voc	λ_P=940nm Ee=0.5mW/c㎡	–	350	—	mV
Total Capacitance	C_T	V_R=3V f=1MHZ Ee=0mW/c㎡	—	20	—	pF
Peak Wavelength of Max Sensitivity	λsmax		—	940	—	nm
Rise Time,Fall Time	tr,tf	V_R=10V R_L=1KΩ	—	50	—	ns